

## ET61H61XX - High Input Very-Low IQ 150mA LDO

### General Description

ET61H61XX are the high input very low  $I_Q$  150mA LDO with high power supply rejection ratio (PSRR).

It operates from 5V~60V. The quiescent current is 2.1 $\mu$ A with no load. The devices feature integrated short-circuit, over-current and over-temperature protection. They are quite suitable for standby microprocessor control-unit systems.

ET61H61XX have a fast response to line transients and load transients, and ensure that no overshoot voltage during start-up and short-circuit recovery of the ET61H61XX.

The ET61H61XX family are available in standard fixed output voltages of 3.0V (ET61H6130), 3.3V (ET61H6133), 3.6V (ET61H6136), 5.0V (ET61H6150), 12V (ET61H61120) and etc.

ET61H61XX family are offered SOT89-3, SOT23-5, SOT23-3 packages.

### Features

- Wide Input Voltage Range: 5V to 60V
- Up to 150mA Load Current
- Standard Fixed Output Voltage Options are 3.0V, 3.3V, 3.6V, 5.0V, and 12V
- Very Low  $I_Q$ : 2.1 $\mu$ A
- Other Output Voltage Options Available on Request
- Low Dropout: Low Dropout is 600mV at 100mA Load@ $V_{OUT}=5V$
- Very High PSRR: 70dB at 1KHz
- Over-Temperature Protection
- Current-Limit Protection
- Short-Circuit Protection
- Excellent Load/Line Transient Response
- Packages are SOT89-3, SOT23-5, SOT23-3

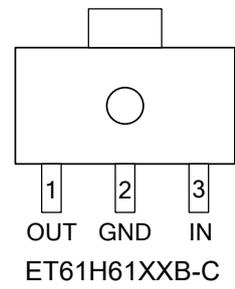
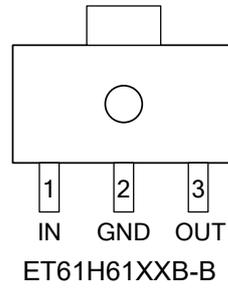
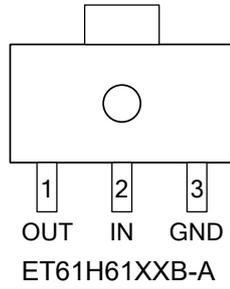
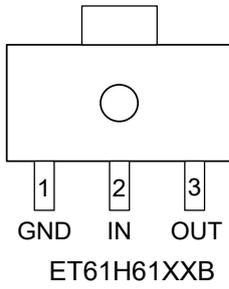
### Device information

ET 61H61 XX X

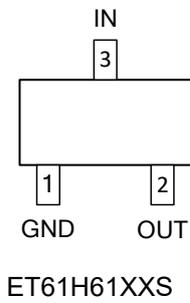
<u>XX</u>	Output Voltage	<u>X</u>	Package
XX	Output X.X V	B	SOT89-3
		S	SOT23-3
		T	SOT23-5
		E	SOT23-5

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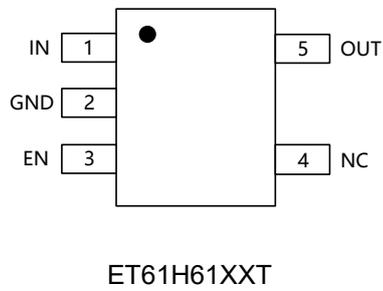
## Pin Configuration



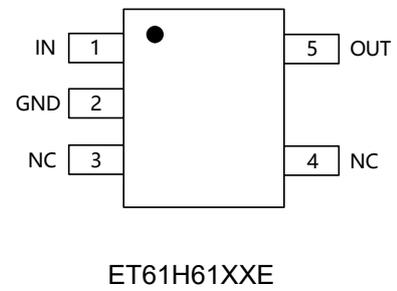
**SOT89-3**



**SOT23-3**



**SOT23-5**



**SOT23-5**

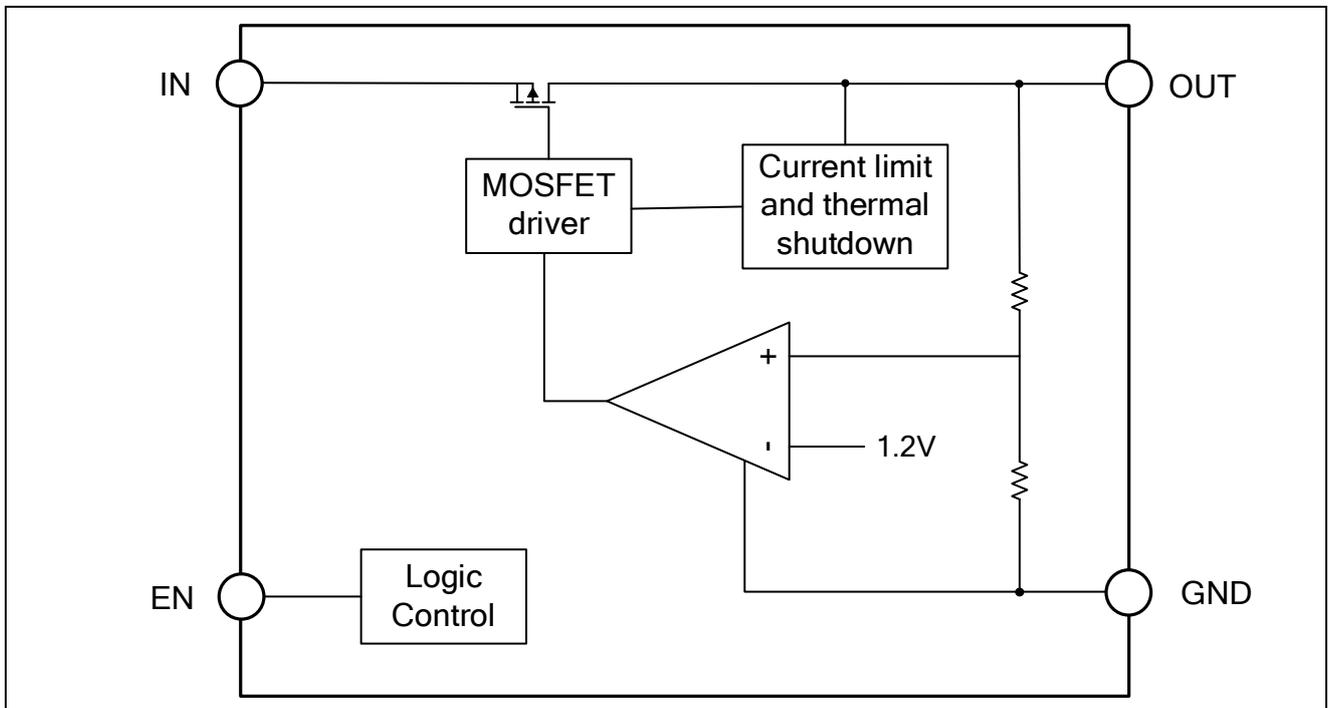
Top View

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## Pin Function

Pin No.							Pin Name	Pin Function
SOT89-3				SOT23-3	SOT23-5			
XXB	XXB-A	XXB-B	XXB-C	XXS	XXT	XXE		
1	3	2	2	1	2	2	GND	Ground.
2	2	1	3	3	1	1	IN	Supply input pin.
3	1	3	1	2	5	5	OUT	Output pin.
					3		EN	Enable control input, active high.
					4	3/4	NC	No connection.

## Block Diagram



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## Functional Description

### Input Capacitor

It is recommended to connect a 1 $\mu$ F capacitor between the VIN and GND pins to eliminate input power fluctuations and reduce output ripple. This input capacitor must be as close to the chip as possible to ensure stable input and output. For PCB layout, note that both VIN and GND require wide copper wires. For high-voltage input ( $V_{IN} \geq 18V$ ) applications, you are advised to use an electrolytic capacitor at the input end or connect a resistor of at least 1 ohm in series at the front end of the input capacitor (the resistor must be adjusted according to the actual application) to prevent chip failure caused by input overshoot.

### Output Capacitor

An output capacitor is required for the stability of the LDO. The recommended output capacitance is from 1 $\mu$ F to 10 $\mu$ F, Equivalent Series Resistance (ESR) is from 5m $\Omega$  to 100m $\Omega$ , and temperature characteristics are X7R or X5R. Higher capacitance values help to improve load/line transient response. The output capacitance may be increased to keep low undershoot/overshoot. Place output capacitor as close as possible to OUT and GND pins.

### Enable

The ET61H61XX (Only SOT23-5 package) delivers the output power when it is set to enable state. When it works in disable state, there is no output power and the operation quiescent current is almost zero. The enable pin (EN) is active high.

### Dropout Voltage

The ET61H61XX uses a PMOS pass transistor to achieve low dropout. When ( $V_{IN} - V_{OUT}$ ) is less than the dropout voltage ( $V_{DROP}$ ), the PMOS pass device is in the linear region of operation and the input-to-output resistance is the  $R_{DS(ON)}$  of the PMOS pass element.  $V_{DROP}$  scales approximately with output current because the PMOS device behaves like a resistor in dropout mode. As with any linear regulator, PSRR and transient response degrade as ( $V_{IN} - V_{OUT}$ ) approaches dropout operation.

### Thermal Shutdown

Thermal shutdown protection disables the output when the junction temperature rises to approximately 150°C. Disabling the device eliminates the power dissipated by the device, allowing the device to cool. When the junction temperature cools to approximately 125°C, the output circuitry is again enabled. Depending on power dissipation, thermal resistance, and ambient temperature, the thermal protection circuit may cycle on and off. This cycling limits regulator dissipation, protecting the LDO from damage as a result of overheating. Activating the thermal shutdown feature usually indicates excessive power dissipation as a result of the product of the ( $V_{IN} - V_{OUT}$ ) voltage and the load current. For reliable operation, limit junction temperature to 125°C maximum.

### Thermal Considerations

For continuous operation, do not exceed absolute maximum junction temperature. The maximum power dissipation depends on the thermal resistance of the IC package, PCB layout, rate of surrounding airflow, and difference between junction and ambient temperature. The maximum power dissipation can be calculated by the following formula:

$$P_{D(MAX)} = (T_{J(MAX)} - T_A) / \theta_{JA}$$

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where  $T_{J(MAX)}$  is the maximum junction temperature,  $T_A$  is the ambient temperature, and  $\theta_{JA}$  is the junction to ambient thermal resistance. The maximum power dissipation depends on the operating ambient temperature for fixed  $T_{J(MAX)}$  and thermal resistance,  $\theta_{JA}$ .

## Current-Limit Protection

The ET61H61XX provides current limit function to prevent the device from damages during over-load or shorted-circuit condition. This current is detected by an internal sensing transistor.

## Absolute Maximum Ratings

Symbol	Rating	Value	Unit
$V_{IN}$	Input Voltage	-0.3~80	V
$V_{OUT}$	Output Voltage	-0.3~12	V
$V_{IN-V_{OUT}}$	Input to Output Voltage	75	V
$V_{EN}$	Chip Enable Input	-0.3~80 & $\leq V_{IN}$	V
$T_{J(MAX)}$	Maximum Junction Temperature	150	°C
$T_{STG}$	Storage Temperature	-40~150	°C
$V_{ESD}$	Human Body Model HBM (ESDA/JEDEC JS-001-2017)	±4000	V
	Charged Device Model (ESDA/JEDEC JS-002-2014)	±200	V
$I_{LU}$	Latch up Current Maximum Rating (JEESD78E)	TBD	mA

## Thermal Characteristics

Symbol	Package	Ratings	Value	Unit
$R_{\theta JA}$	SOT89-3	Thermal Characteristics, Thermal Resistance, Junction-to-Air	130	°C/W
	SOT23-5		200	
	SOT23-3		200	
$P_D$	SOT89-3	Power Dissipation@25°C PCB board dimension: 50mm x 50mm (2layer) Copper :1oz	900	mW
	SOT23-5		600	
	SOT23-3		600	

## Recommended Operating Conditions

Symbol	Item	Rating	Unit
$V_{IN}$	Input Voltage	5 to 60	V
$I_{OUT}$	Output Current	0 to 150	mA
$T_A$	Operating Ambient Temperature	-40 to 85	°C
$T_J$	Operating Junction Temperature	-40 to 125	°C
$C_{IN}$	Effective Input Ceramic Capacitor Value	1~10	μF
$C_{OUT}$	Effective Output Ceramic Capacitor Value	1~10	μF
ESR	Input and Output Capacitor Equivalent Series Resistance (ESR)	5 to 100	mΩ

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## Electrical Characteristics

( $V_{IN} = V_{OUT} + 2V$ ;  $I_{OUT} = 10mA$ ,  $C_{IN} = 1.0\mu F$ ,  $C_{OUT} = 10\mu F$ , unless otherwise noted. Typical values are at  $T_A = +25^\circ C$ .)

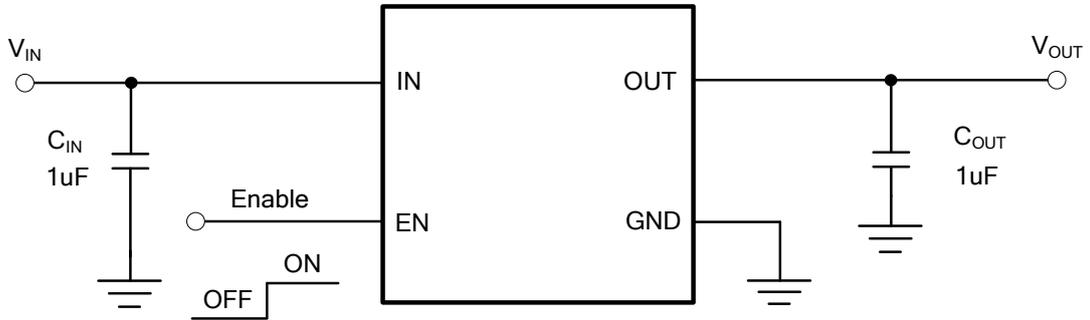
Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_{IN}$	Operating Input Voltage		5		60	V
$V_{OUT}$	Output Voltage	$V_{IN} = 12V$ , $I_{OUT} = 10mA$	-2%		+2%	V
$I_{Q\_ON}$	Quiescent Current	$V_{IN} = 12V$ , $I_{OUT} = 0mA$	1.9	2.1	2.3	$\mu A$
$Reg_{Line}$	Line Regulation	$V_{IN} = V_{OUTNOM} + 0.5V$ to 60V, $I_{OUT} = 1mA$		0.1		mV/V
$V_{DROP}^{(1)}$	Dropout Voltage	$I_{OUT} = 10mA$ , $V_{OUT} = 3.3V$ $T_A = +25^\circ C$		70		mV
		$I_{OUT} = 100mA$ , $V_{OUT} = 3.3V$ $T_A = +25^\circ C$		650		
		$I_{OUT} = 10mA$ , $V_{OUT} = 5.0V$ $T_A = +25^\circ C$		60		
		$I_{OUT} = 100mA$ , $V_{OUT} = 5.0V$ $T_A = +25^\circ C$		600		
$Reg_{LOAD}$	Load Regulation	$1mA \leq I_{OUT} \leq 150mA$ , $V_{IN} = V_{OUT} + 2V$		0.1		mV/mA
$I_{LMT}$	Current Limit			250		mA
$I_{SHORT}$	Short Current Limit	$V_{IN} = 12V$ , $V_{OUT} = 0V$		80		mA
$PSRR^{(2)}$	Power Supply Rejection Ratio	$f = 1\text{ kHz}$ , $V_{IN} = 10V$ $I_{OUT} = 10mA$ , $V_{OUT} = 3.3V$		70		dB
$T_{TSD}^{(2)}$	Thermal Shutdown Temperature	Temperature Increasing from $T_A = +25^\circ C$		150		$^\circ C$
$T_{HYS}^{(2)}$	Thermal Shutdown Hysteresis	Temperature Falling from $T_{TSD}$		35		$^\circ C$

**Note1.**  $V_{DROP}$  FT test method: test the  $V_{OUT}$  voltage at  $V_{OUT} + V_{DROPMAX}$  with 150mA output current.

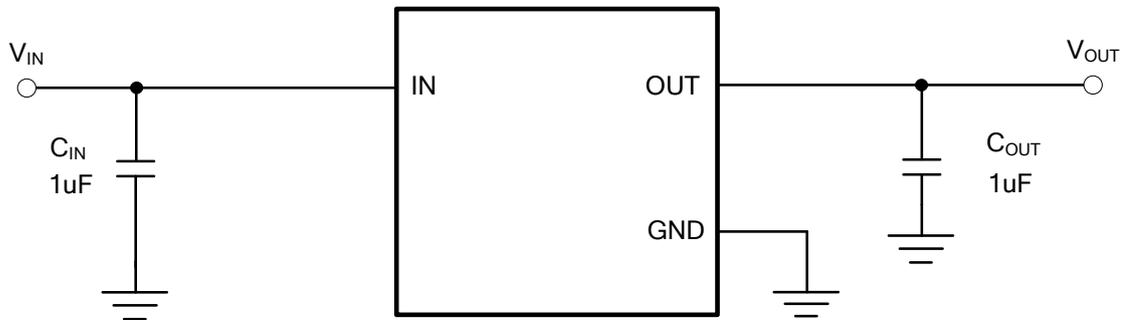
**Note2.** Guaranteed by design and characterization. not a FT item.

# ET61H61XX

## Application Circuits



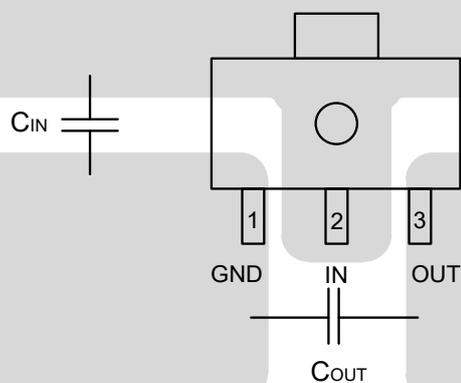
With EN Function



Without EN Function

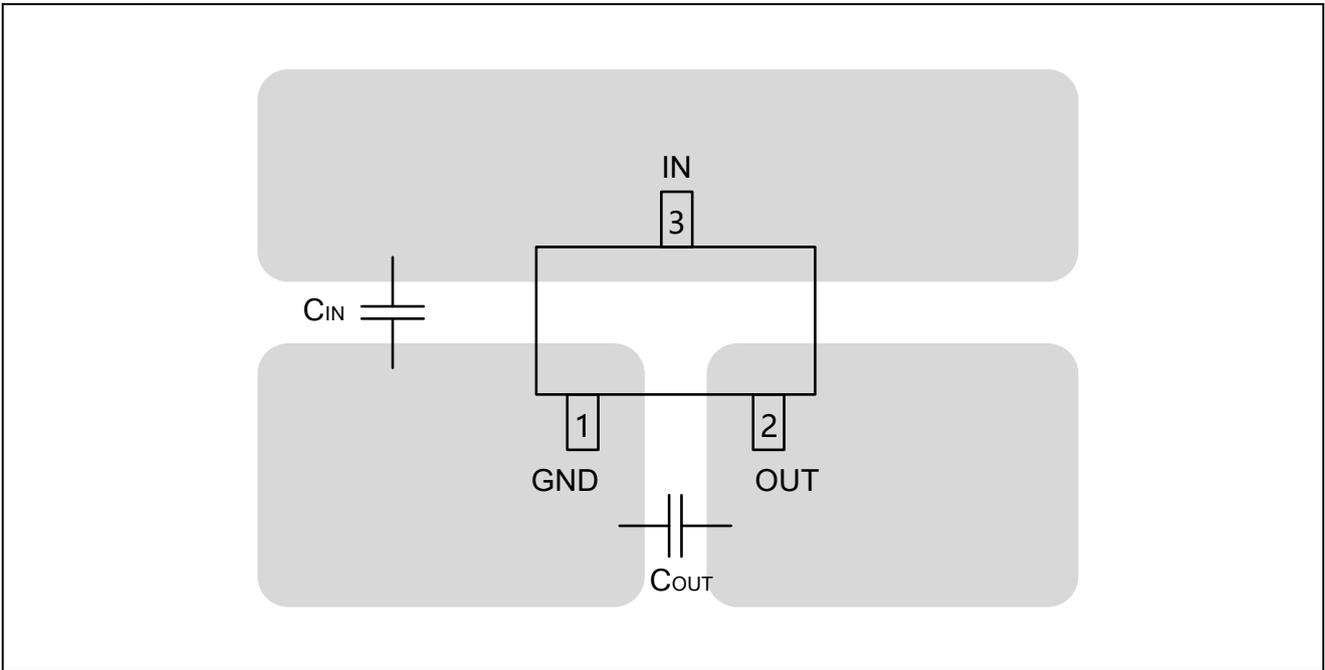
## PCB Layout Guide

SOT89-3 (ET61H61XXB)

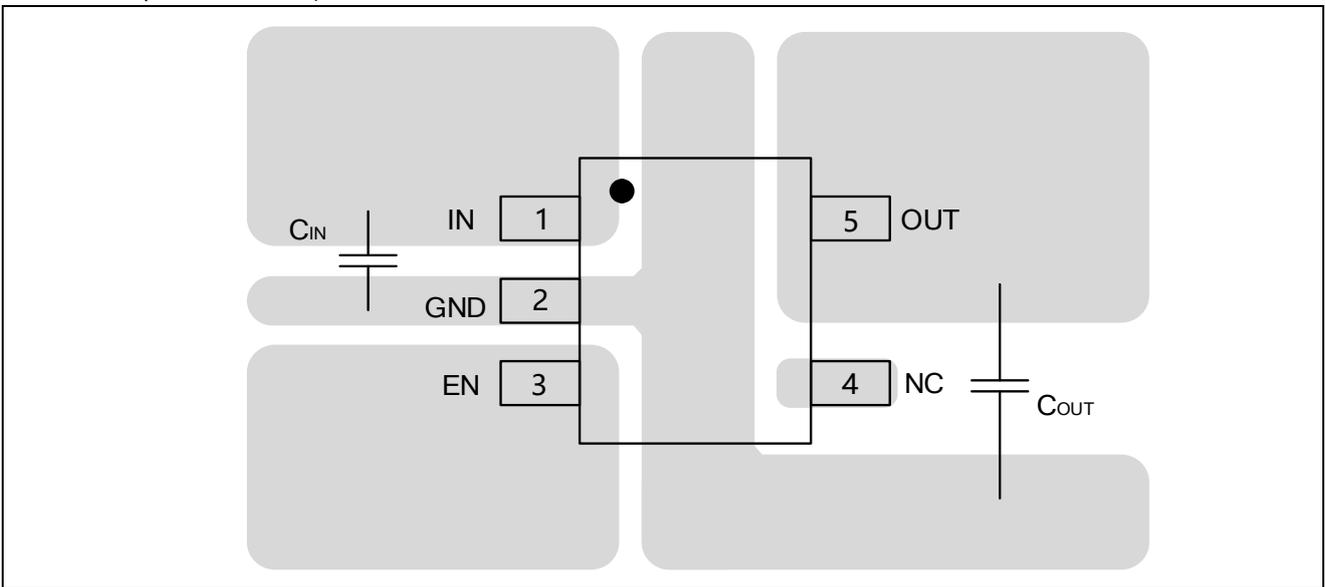


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SOT23-3 (ET61H61XXS)



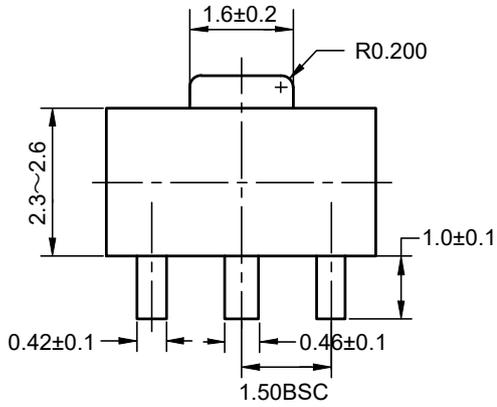
SOT23-5 (ET61H61XXT)



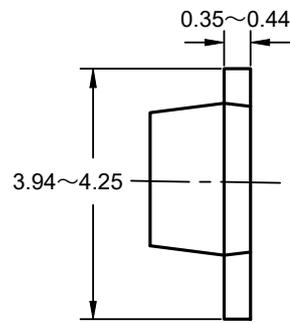
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## Package Dimension

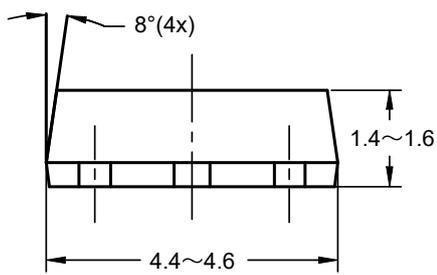
SOT89-3



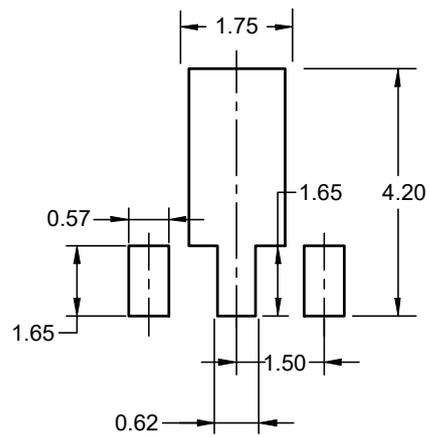
Top View



Side View



Side View

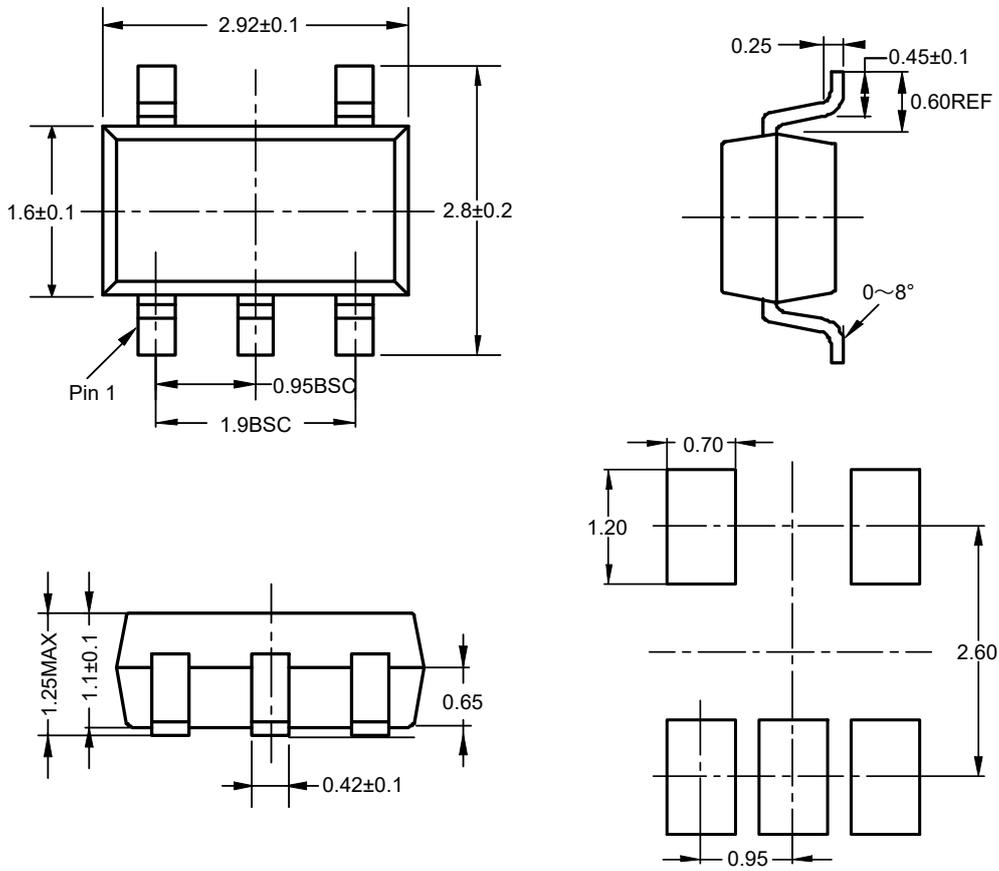


Recommended Land Pattern

Unit: mm

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SOT23-5

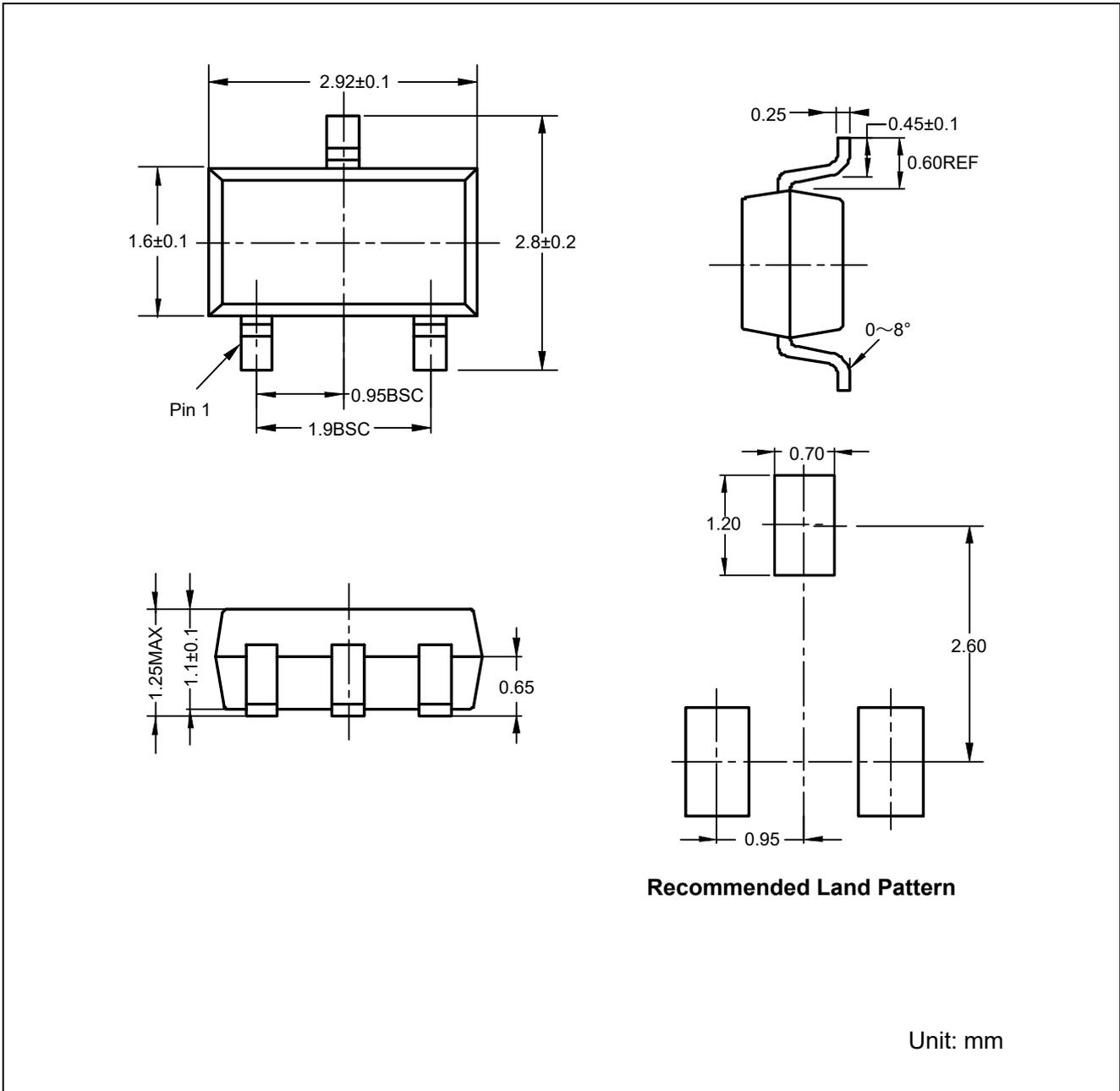


**Recommended Land Pattern**

Unit: mm

# ET61H61XX

SOT23-3



## Revision History and Checking Table

Version	Date	Revision Item	Modifier	Function & Spec Checking	Package & Tape Checking
0.0	2023-12-17	Preliminary Version	Marj	Tugz	Liuju
1.0	2024-1-12	Offered Version	Marj	Tugz	Liuju